

ABSTRACT OF THE DISCLOSURE

This invention improves TFT characteristics by making an interface between an active layer, especially a region forming a channel formation region and an insulating film excellent, and provides a semiconductor device provided with a semiconductor circuit
5 made of a semiconductor element having uniform characteristics and a method of fabricating the same. In order to achieve the object, a gate wiring line is formed on a substrate or an under film, a gate insulating film, an initial semiconductor film, and an insulating film are formed into a laminate without exposing them to the atmosphere, and after the initial semiconductor film is crystallized by irradiation of infrared light or
10 ultraviolet light (laser light) through the insulating film, patterning is carried out to obtain an active layer and a protection film each having a desired shape, and then, a resist mask is used to fabricate the semiconductor device provided with an LDD structure.